

References

- [1] C. Downs and T. E. Vandervelde, “Progress in Infrared Photodetectors Since 2000,” *Sensors*, vol. 13, pp. 5054–5098, Apr. 2013. Number: 4 Publisher: Multidisciplinary Digital Publishing Institute.
- [2] W. K. Liu, W. T. Yuen, and R. A. Stradling, “Preparation of InSb substrates for molecular beam epitaxy,” *Journal of Vacuum Science & Technology B: Microelectronics and Nanometer Structures Processing, Measurement, and Phenomena*, vol. 13, pp. 1539–1545, July 1995.
- [3] A. J. Noreika, M. H. Francombe, and C. E. C. Wood, “Growth of Sb and InSb by molecular-beam epitaxy,” *Journal of Applied Physics*, vol. 52, pp. 7416–7420, Dec. 1981.
- [4] S. Massidda, A. Continenza, A. J. Freeman, T. M. de Pascale, F. Meloni, and M. Serra, “Structural and electronic properties of narrow-bandgap semiconductors: InP, InAs, and InSb,” *Physical Review B*, vol. 41, pp. 12079–12085, June 1990. Publisher: American Physical Society.
- [5] Y. Song, Y. Gu, J. Shao, and S. Wang, “Dilute Bismides for Mid-IR Applications,” in *Bismuth-Containing Compounds* (H. Li and Z. M. Wang, eds.), Springer Series in Materials Science, pp. 1–27, New York, NY: Springer, 2013.
- [6] D. Kandel and E. Kaxiras, “The Surfactant Effect in Semiconductor Thin-Film Growth,” vol. 54, pp. 219–262, 2000. Book Title: Solid State Physics ISBN: 9780126077544 Publisher: Elsevier.
- [7] J. M. Millunchick and C. R. Tait, “Surface Mediated Growth of Dilute Bismides,” in *Bismuth-Containing Alloys and Nanostructures* (S. Wang and P. Lu, eds.), Springer Series in Materials Science, pp. 201–214, Singapore: Springer, 2019.
- [8] J. Massies and N. Grandjean, “Surfactant effect on the surface diffusion length in epitaxial growth,” *Physical Review B*, vol. 48, pp. 8502–8505, Sept. 1993. Publisher: American Physical Society.
- [9] S. Wang and P. Lu, eds., *Bismuth-Containing Alloys and Nanostructures*, vol. 285 of *Springer Series in Materials Science*. Singapore: Springer, 2019.
- [10] A. Bakarov, Y. Galitsyn, V. Mansurov, and K. Zhuravlev, “Reconstruction phase transition c(4×4) – (1×3) on the (001)InSb surface,” *Journal of Crystal Growth*, vol. 457, pp. 207–210, Jan. 2017.
- [11] J. J. Bomphrey, M. J. Ashwin, T. S. Jones, and G. R. Bell, “The c(4 × 4)-a(1 × 3) surface reconstruction transition on InSb(0 0 1): Static versus dynamic conditions,” *Results in Physics*, vol. 5, pp. 154–155, Jan. 2015.